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16. (Amended) A method for fabricating a film, the method comprising:
supplying electrical energy to a mixture of noble gas and reactant gas at a total pressure of 1 kPa to 110 kPa to create reactive species, the reactive species forming a film on a substrate, the electrical energy being used for producing noble gas radicals and ions, the noble gas radicals and ions colliding with the reactant gas to form the reactive species.

17. (Amended) A method for fabricating a film, the method comprising:
supplying optical energy with a light of wavelength less than 200 nanometer to a mixture of noble gas and reactant gas to create reactive species, the reactive species forming a film on a substrate, the electrical energy being used for producing noble gas radicals and ions, the noble gas radicals and ions colliding with the reactant gas to form the reactive species.

20. (Amended) A method for fabricating a semiconductor device, the method comprising:

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a step of forming a film by supplying electrical energy to a mixture of noble gas and reactant gas at a total pressure of 90 kPa to 110 kPa to create reactive species, the reactive species forming a film on a substrate, the electrical energy being used for producing noble gas radicals and ions, the noble gas radicals and ions colliding with the reactant gas to form the reactive species.

21. (Amended) A method for fabricating a memory device, the method comprising:

a step of forming a film by supplying electrical energy to a mixture of noble gas and reactant gas at a total pressure of 90 kPa to 110 kPa to create reactive species, the reactive species forming a film on a substrate, the electrical energy being used for producing noble gas radicals and ions, the noble gas radicals and ions colliding with the reactant gas to form the reactive species.

Please add new claim 22 as follows:

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--22. (New) A method for fabricating a film according to claim 2, the electric power being applied through electrodes, the distance between the electrodes being less than 5mm.--

REMARKS

Claims 1-22 are pending. By this Amendment, the title and claims 1, 16, 17, 20 and 21 are amended and new claim 22 is added.